

[TuA1] Growth and Characterization of BN

Date / Time May 24 (Tue.), 2022 / 14:15–16:15

Place Convention Hall A

Session Chair Jong-Hwan Kim (POSTECH, Korea)

[TuA1-1] Invited Talk

Online 14:15–14:45

The Emergence of Hexagonal Boron Nitride Material as an Enabler for Next Generation III–Nitride Devices

Suresh Sundaram^{1,2,3}, Phuong Vuong², Soufiane Karrakchou^{1,2}, Adama Mballo², Ashutosh Srivastava^{1,2}, Gilles Patriarche⁴, Paul L. Voss^{1,2}, Jean Paul Salvestrini^{1,2,3}, Abdallah Ougazzaden^{1,2}

¹*Georgia Institute of Technology, USA*, ²*CNRS, France*, ³*Georgia Tech Lorraine, France*,

⁴*University of Paris-Saclay, France*

[TuA1-2] Oral

Online 14:45–15:05

The Optical Properties of Polytypes of sp²-Bonded Boron Nitride

Bernard Gil¹, James H. Edgar², Jiahua Li², Matthieu Moret¹, Adrien Rousseau¹, Pierre Valvin¹, Guillaume Cassabois¹, Wilfried Desrat¹, Sachin Sharma³, Laurent Souqui⁴, Henrik Pedersen³, Hans Höglberg³

¹*CNRS-The University of Montpellier, France*, ²*Kansas State University, USA*, ³*Linköping University, Sweden*, ⁴*University of Illinois Urbana-Champaign, USA*

[TuA1-3] Oral

Online 15:05–15:25

Novel 2D Layered Boron Rich B(Al)N Ternary Alloys: Epitaxial Growth and Materials Characterization

P. Vuong¹, A. Mballo¹, S. Sundaram^{1,2,3}, G. Patriarche⁴, Y. Halfaya⁵, T. Moudakir⁵, S. Gautier⁵, P. L. Voss^{1,2}, J. P. Salvestrini^{1,2,3}, A. Ougazzaden^{1,2}

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[TuA1-4] Oral

Offline 15:25–15:45

Epitaxial Growth of Large-Area Single-Crystal Few-Layer Hexagonal Boron Nitride Film on Ni (111)

Kyung Yeol Ma^{1,2}, Leining Zhang^{1,2}, Rodney S. Ruoff^{1,2}, Manish Chhowalla³, Feng Ding^{1,2}, Hyeyon Suk Shin^{1,2}

¹*Ulsan National Institute of Science and Technology, Korea*, ²*Institute for Basic Science, Korea*,

³*University of Cambridge, UK*

[TuA1-5] Invited Talk

Offline 15:45–16:15

Growth of Monolayer and Few-Layer Hexagonal Boron Nitride by Chemical Vapor Deposition

Hyeyon Suk Shin

Ulsan National Institute of Science and Technology, Korea